

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) BREV 12370 C	Application Number		
				Applicant(s) ASPAR ET AL			
				Filing Date	Group Art Unit		
				2823			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Drc		5,256,581	10/26/93	FOERSTNER ET AL	437	24	
Drl		6,020,252	2/1/00	ASPAR ET AL	438	458	
							11093 U.S. PRO 11093/117516
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
EXAMINER				DATE CONSIDERED			
D.R. COURL				12-21-01			

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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dmc		4,704,302	11/3/87	Bruel et al			
		5,234,535	8/10/93	NBeyer et al			
		5,494,835	2/27/96	Bruel			
		5,804,086	9/8/98	Bruel			
		5,817,368	10/6/98	Hashimoto			
		5,863,830	1/26/99	Bruel et al			
		5,897,331	4/27/99	Sopori			
		5,633,174	5/27/97	Li			
Y		5,250,446	10/5/93	Osowa et al			

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							YES	NO
Dmc		WO95/20824	8/3/95	PCT			✓	
		EP 0703 609	3/27/96	EPO			✓	
		0 660 140	6/28/95	EPO			✓	
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FORM PTO-1449	SERIAL NO.	CASE NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE	BREV 12370 CON 2 GROUP ART UNIT
	APPLICANT(S):	Aspar et al.

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

U.S. PATENTS

<u>PATENT NO.</u>	<u>INVENTOR</u>	<u>ISSUE DATE</u>
4,179,324	12/18/79	Kirkpatrick
5,110,748	5/5/92	Sarma
5,310,446	5/10/94	Konishi et al.
5,661,333	8/26/97	Brue et al.

DAC

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<u>DOCUMENT NO.</u>	<u>COUNTRY</u>	<u>DATE</u>
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OTHER PUBLICATIONS

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FORM PTO-1449		SERIAL NO. 777516	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		FILING DATE 2/6/01	GROUP ART UNIT 2823
(use several sheets if necessary)		APPLICANT(S): Aspar et al.	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
Dmc	A1 4,179,324	12/18/79	Kirkpatrick	156/230	11/28/77
	A2 5,110,748	5/5/92	Sarma	437/51	7/22/91
	A3 5,310,446	5/10/94	Konishi et al.	117/58	7/13/92
↓	A4 5,661,333	8/26/97	Bruel et al.	257/618	1/25/95
	A5				
	A6				
	A7				
	A8				

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES	NO
Dmc	A9 2725074	3/29/96	France			X
↓	A10 0355913	2/28/90	EPO		X	
↓	A11 0504714	9/23/92	EPO		X	

EXAMINER INITIAL	OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
Dmc	A12	Silicon-On-Insulator, <i>European Semiconductor</i> , March, 1997, pages 17 and 18
	A13	Aspar et al., SMART-CUT®: The basic fabrication process for UNIBOND® SOI wafers, <i>SEM/1996</i> , pp. 37-46
	A14	Klem et al., Characteristics of lift-off fabricated AlGaAs/InGaAs single-strained quantum well structures on glass and silicon substrates, <i>Inst. Phys. Conf.</i> , Ser. No 96: Chapter 6, pp. 387-392
	A15	Hamaguchi et al., Device Layer Transfer Technique using Chemi-Mechanical Polishing," <i>Japanese Journal of Applied Physics</i> , 23(1984), Oct., No. 10, Part 2, Tokyo, Japan, pp. L815-L817
↓	A16	Haisma et al., Silicon-on-Insulator Wafer Bonding-Wafer Thinning Technological Evaluations, <i>Japanese Journal of Applied Physics</i> , 28(1989), Aug., No. 8, Part 1, Tokyo, Japan, pp. 1426-1443

EXAMINER	D.M. Colurs	DATE CONSIDERED	12-21-01
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Dpe</i>		4,931,405	06/05/1990	KAMIJO ET AL	437	12	
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INFORMATION DISCLOSURE STATEMENT
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	A.J. AUBERTON-HERVE ET AL., SOI MATERIALS FOR ULSI APPLICATION, 1995,
↓	M. BRUEL ET AL, "SMART-CUT": A PROMISING NEW SOI MATERIAL TECHNOLOGY, 1995, PAGES 178-179

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<i>Done</i>		Comparative study of annealed neon-, argon-, and krypton- ion implantation damage in silicon, A.G. Cullis, T. E. Seidel and R.L. Meek, J. Appl. Phys. 49(10) October 1978, pgs. 5188 - 5198
<i>Done</i>		Equilibrium Shape of Si, Eaglesham, White, Feldman, Moriya nd Jacobson, Physical Review Letters, Volume 70, Number 11, March 15, 1993, pgs. 1643-1646

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FORM PTO-1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. BREV 12370 CON 2	SERIAL NO. 777516
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) (37 CFR 1.98(b))		APPLICANT ASPAR ET AL	
		FILING DATE 276/01	GROUP 2823

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DNC		"Silicon on insulator Material Technology" Bruel, M.
		Electronic Letters; 31 (1995) 06 July; No. 14; pgs 1201-1202
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		Japan Allied Physics; 64(8); October 15, 1988; pgs. 3972-3974

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